



Thin films of graphene decorated with NiS₂ hybrid sensor for detection of NO₂ gas

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ABSTRACT

Here, we demonstrate the improved NO₂ gas-sensing properties based on graphene-decorated NiS₂ thin film. The grown NiS₂ thin film, graphene was spread over NiS₂ thin film by chemical vapour deposition (CVD) method. The formation of several p–n heterojunctions is greatly affected by the current–voltage relation of graphene-decorated NiS₂ thin film due to p-type and n-type nature of graphene and NiS₂, respectively. Initially with graphene decoration on NiS₂ thin film, current decreases in comparison to NiS₂ thin film, whereas depositing graphene film on glass substrate, current increases drastically. The NO₂ gas sensor device is fabricated and its basic characteristics are systematically investigated. The incorporated graphene improves the NO₂ sensing response of 97% with compared to bare NiS₂ sensor (29%) at 100 ppm NO₂ concentration with a practical detection limit below 0.2 ppm. In addition, the recovery time was shortened to a few seconds and the excellent repeatability. This work may provide a promising and practical method to mass produce room-temperature NO₂ gas sensors for real-time environment monitoring due to its simple fabrication process, low cost, and practicality. The high-sensing response of NiS₂/graphene is attributed to the formation and modulation of p–n heterojunction at the interface of graphene and NiS₂. In addition, the presence of active sites graphene surface also enhances the sensing response.

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1 Introduction

Gas sensors are generally understood as providing a measurement of the concentration of some analyte of interest, such as CO, CO₂, NO_x, SO₂, without at this point dwelling on the plethora of underlying approaches such as optical absorption, electrical conductivity, electrochemical (EC), and catalytic bead. Gas sensors are devices that help us understand the amount of gas in the environment and the natural state of its movement. Gas sensors reveal the amount of gas in the environment and the nature of the gas composition with electrical signals and can provide its change [1–4]. Currently, environmental pollution has created huge trouble due to its harmful effects on all living organisms. Nitrogen dioxide (NO₂) is one of the most known air pollutant in the environment whose major emission is from industrial waste, automobile by-products, and power plants [1–3]. Further, the formation of acid rain takes place when NO₂ interacts with water molecules in the atmosphere, resulting in serious harm to the ecosystem [5]. In addition, the continued inhalation of NO₂ to gives rise to throat irritation, lung infections and reduces the capability of the respiratory system [6–8]. Therefore, the enlargement of highly sensitive and selective NO₂ gas sensors has become an utmost necessity for timely detection of the harmful gas even at extremely low concentration around 1 ppm. To suffice the demand of efficient gas sensors, the need of metal oxide semiconductor based gas sensors for precise detection of NO₂ gas emerges [9, 10]. The demand for highly sensitive and reliable chemiresistive-based NO₂ sensor has been increasing over the last few years. In response to this demand, huge effort has been made to develop and design high surface area electrodes with good physico-chemical properties [11]. Numerous materials belonging to transition metal oxides/sulfides, doped metal oxides, metal hydrides, and polymeric materials have been used for fabricating sensing materials [12–16]. Among these materials, nickel sulphides are considered to be productive semiconducting materials for sensor applications not only because of their chemical sensitivity to liquid as well as major gases, its low-cost, nontoxic nature, high chemical stability and greater natural abundance. Sulfides of various transition metals show interesting electrical and optical properties such as semiconductivity, luminescence,

gas sensors and photoconductivity. NiS₂ demonstrates excellent potential for NO₂ identification at room temperature [17]. NiS₂ has also been emerging as a promising material, which also shows great potential because of their high conductivity [18]. However, improving the sensing performances of nickel sulfides is still a challenge. Therefore, the present approach for nickel sulfides is to increase the electronic conductivity. On the other hand, carbon nanotubes and graphene have been extensively studied because of their exceptional physical characteristics, such as their large surface areas, exceptional chemical stabilities, outstanding electronic properties and potential applications in sensors. The introduction of graphene and other carbon support materials during the preparation of nickel sulfides has proven to be an effective strategy to prevent the aggregation of nickel sulfide particles and provide more effective interconnected networks for electron transport [19]. As widely reported in the literature, graphene prepared from multiple approaches that include mechanical exfoliation, chemical vapor deposition, and epitaxial growth has shown a low limit of detection, small noise, and good reversibility [20, 21]. Recently, NiS₂ has been reported as a good material for gas sensing [22], since its hybridization with graphene to form composite/hybrid materials results in high sensitivity due to synergistic effects and solves the problem of slow graphene-only sensor recovery [23–27]. In addition, direct deposition of NiS₂ on graphene using high-temperature chemical vapor deposition (CVD) affords sensors with increased thermal stability. Moreover, NiS₂ with preferentially exposed active edge sites has been reported to be more active than that with exposed basal planes. Hence, we herein use thermal CVD to deposit NiS₂ on graphene, utilizing the fabricated hybrid materials to detect NO₂ gas at very low concentration and determining the properties of the prepared sensor. Furthermore, the structure, morphology and sensing characteristics of the hybrid composites were investigated in detail. The NiS₂ gas sensor responded with a 28% change upon being exposed to 100 ppm of NO₂, while the response of the NiS₂/graphene device reached 97% when exposed to the same NO₂ concentration. Moreover, the fabricated sensor showed long term stability and high selective response towards NO₂ gas than compared with other gaseous species. The improved sensing mechanism of the proposed sensor was also

discussed in detail. The synthetic strategy reported here may provide new opportunities to improve the sensing properties of NiS₂/graphene composites.

2 Experimental details

2.1 Materials

Nickel sulphide thin films were prepared from aqueous solution of nickel chloride (NiCl₂) and sodium tetrathiolphate (Na₂S₂O₃·5H₂O) as sources of Ni²⁺ and S₂[−] ions respectively. All the chemicals used were of analytical grade and all the solutions were prepared in de-ionized water. Ammonia (NH₃) solution was used as a complexing agent during the deposition.

2.2 Fabrication of pristine NiS₂ and NiS₂/graphene thin films

Based on the previous literature work, the bare graphene was synthesized from graphite powder using a hydrothermal method [28]. In a typical synthesis of NiS₂, the original molar ratio between NiCl₂·2H₂O and Na₂S₂O₃·5H₂O was selected to be 1:3. NiCl₂·2H₂O (0.28 g, 0.001 M) was dissolved in deionized water (30 mL). The chelating agent, triethanolamine (12 mL ≈ 0.003 M), was added to the solution. NaOH (1.0 g, 0.025 M) was added to keep the pH value at about 10. After mixing for 5 min under stirring, Na₂S₂O₃·5H₂O (0.78 g, 0.003 M) was added to the mixture, and the system finally formed a blue, transparent solution. In a typical synthesis of NiS₂, the original molar ratio between NiCl₂ and Na₂S₂O₃·5H₂O was selected to be 1:3. NiCl₂ (0.30 g, 0.001 M) was dissolved in deionized water (30 mL). The chelating agent, triethanolamine (12 mL ≈ 0.003 M), was added to the solution. NH₃ (0.05 M) was added to keep the pH value at about 9. In the standard horizontal configuration, a quartz tube about 1 m long with a diameter of 2–5 cm is used. The heating resistance is placed around the quartz tube. The solution was ionized by an ultrasonic generator of 1.7 MHz frequency, produced aerosol was carried directly to the heated substrates using compressed air as carrier gas in a flow rate of 5 L/min. The number of spray cycles was optimized to six. After that the deposited FTO substrate was taken out and dried in a dessicator under low vacuum

(approx. 10^{−2} mbar) for 24 h. The as-synthesized films were named as pure NiS₂. In NiS₂/graphene film, 0.5 g of graphite powder was mixed with NiS₂ precursor solution and same experiment was carried out. Finally, the dried FTO film was named as NiS₂/graphene film. Figures S1 and S2 show the schematic representation for the synthesis process of graphene and NiS₂/graphene hybrid thin film. Figure S3 shows the photograph image of fabricated thin films.

2.3 Fabrication of gas sensor set up

Figure 1 shows the fabrication process of a gas sensor device. Alumina plates with silver interdigitated electrodes were used as substrates. The width and interspacing of the electrodes were 0.3 mm and 0.15 mm, respectively. The electrical response of the sensors towards change in LPG gas was recorded using an in-house built controlled environmental chamber. The gas-sensing measurements were performed in a mass flow controlled vacuum chamber which periodically allowed and stopped the flow of gas. Two sides of the electrode were connected to a computer controlled source-meter (Keithley-237), for measurement of the gas sensing curves at room temperature. The sensor response is calculated using $S(\%) = \Delta R/R \times 100$, where ΔR is a difference between the gas and air resistance; R is the gas resistance. The response time was defined as the moment when the resistance of the sensor reached 90% of its final value in the presence of the target gas, and the recovery time was defined as the time needed for the resistance to reach 90% of its initial value after

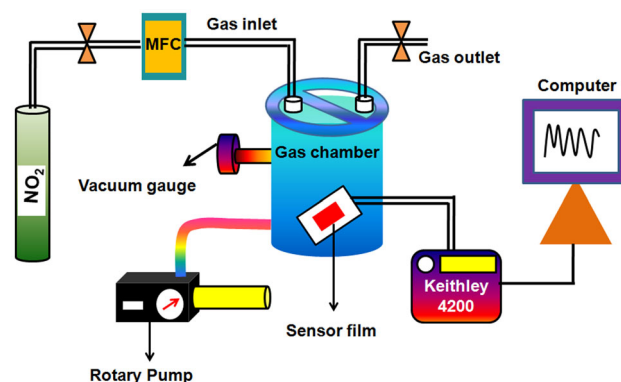


Fig. 1 Schematic representation of the resistive type gas sensor setup

gas stoppage. Figure S4a Photograph of gas sensor set up and b NiS₂ sensor film (Final device), respectively.

3 Results and discussion

3.1 XRD analysis

The phase and crystalline structure of the sensor samples were analyzed by XRD method. Figure 2 shows the XRD pattern of graphene, NiS₂, and NiS₂/graphene films, respectively. The strong diffraction peak at 26.97° is attributed to the (002) planes of graphene [29]. As shown in Fig. 2, the peaks appeared at $2\theta = 26.8^\circ, 31.3^\circ, 36.5^\circ, 38.1^\circ, 45.3^\circ, 49.1^\circ, 52.3^\circ, 53.4^\circ, 58.5^\circ, 61.2^\circ,$ and 67.0° corresponding to the (111), (200), (211), (220), (221), (311), (023), (321), and (400) planes, respectively, which can be clearly indexed to cubic pyrite NiS₂ with lattice parameters of $a = 5.67 \text{ \AA}$, which is consistent with the reported data for NiS₂ (JCPDS # 11-99).

The intensity of (200) diffraction peaks is relatively higher than the conventional value, indicating that the (200) plane of NiS₂ tends to be preferentially oriented in the experimental system. The presence of (002) plane along with NiS₂ diffraction in the composite samples demonstrate that nanocomposites of NiS₂ and graphene was formed. Raman spectra were further carried out to identify the functional groups and graphene hybridization with NiS₂ crystal matrix.

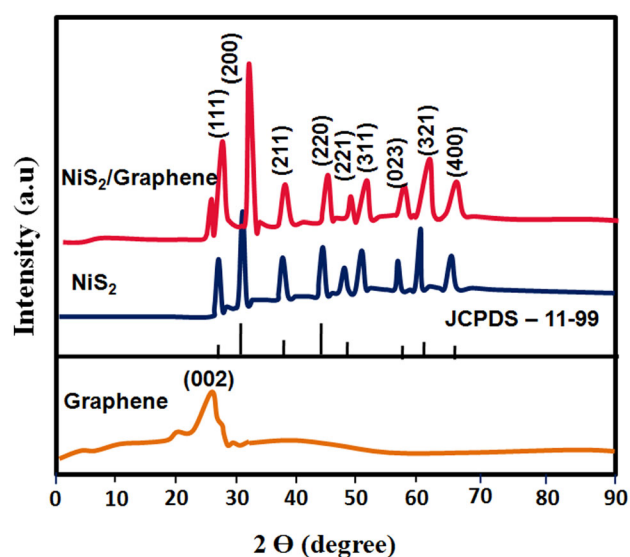


Fig. 2 X-ray diffraction pattern of the sensor samples

3.2 FTIR and Raman analysis

Fourier transform infrared spectroscopy (FTIR) is employed to clarify the functional groups of graphene, NiS₂ and the NiS₂/graphene composite. As shown in Fig. 3a, the peak at 625 cm^{-1} can be attributed to the Ni-S stretching vibration. The multiple peaks at $700\text{--}1150 \text{ cm}^{-1}$ can be assigned to the sulfate groups, while the sharp peaks at 3445 and 1614 cm^{-1} can be ascribed to the O-H stretching and water bending, respectively. For the graphene spectrum, the intense peak located at 1614 cm^{-1} can be attributed to the aromatic C=C (stretching), and the very weak peak located at 1125 cm^{-1} corresponds to the C-O stretching. In contrast, the absence of a C=O peak around 1715 cm^{-1} indicates the insignificant amount of oxidation of graphene. Raman Spectroscopy is a very powerful tool for analyzing the properties of carbon and other two-dimensional materials. It also used to confirm the successful hybridization of carbon with TMDs. The Raman spectra of pure graphene, NiS₂, and NiS₂/graphene composite samples are shown in Fig. 3b. Typically, the NiS₂ film exhibits two Raman characteristic peaks at about 280.6 cm^{-1} and 490.9 cm^{-1} , corresponding to the A_{1g} and E_{2g} modes, respectively [30, 31]. The ratio of the D to G band in the composites is larger than that of graphene due to increased lattice disorder and compared to pure graphene, the D and G bands red-shift because of electron transfer at the interface. The combination Raman modes of NiS₂ and graphene in the composite films further confirms that successful formation heterostructure composite between NiS₂ and graphene.

3.3 Morphological studies

The morphology and structure of the NiS₂/graphene were investigated by SEM and TEM. Typical morphological information of the as grown films is shown in Fig. 4. A sheet-like shape with an average diameter of roughly $2\text{--}3 \text{ }\mu\text{m}$ can be seen in a SEM image of pure graphene (Fig. 4a). The pure NiS₂ sample has irregularly shaped nanograins that are consistently adorned on the surface of the graphene nanosheet in the NiS₂/graphene film, whereas the NiS₂/graphene film has uniformly decorated graphene nanosheets (Fig. 4c). In the TEM image, the crumple type sheet like form of graphene was also discovered (Fig. 4d). The surface of graphene

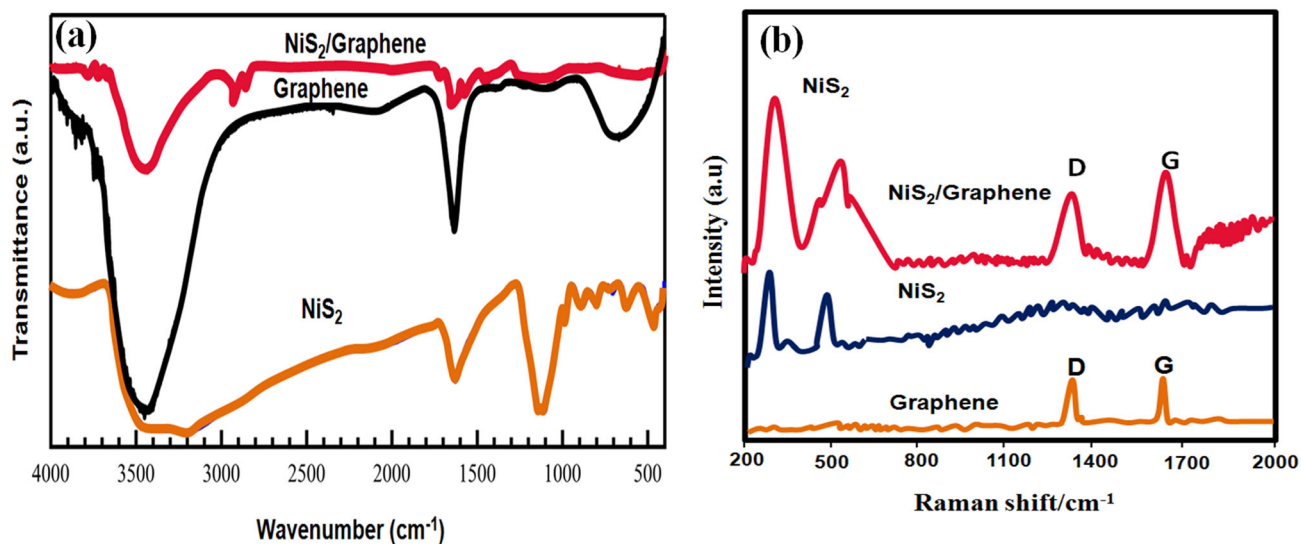
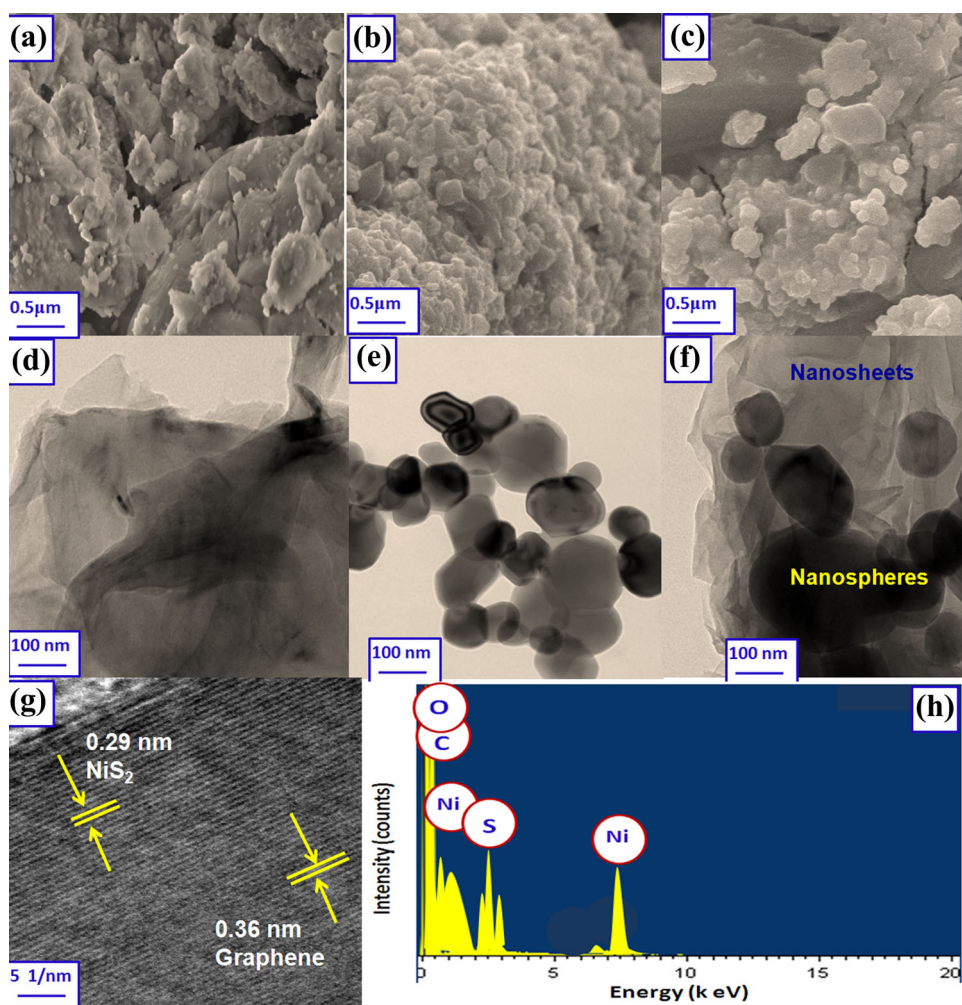


Fig. 3 a FTIR and b Raman spectra of the sensor samples

Fig. 4 SEM images of a graphene, b NiS_2 , c NiS_2/G , TEM images of d graphene, e NiS_2 , f NiS_2/G , g HRTEM of NiS_2/G and h EDS of NiS_2/G



nanosheets was uniformly adorned with spherical shaped NiS₂ nanoparticles with diameters in the range of 30–35 nm (Fig. 4e, f). We used high-resolution transmission electron microscopy (HR-TEM) to examine the microstructure of the NiS₂/graphene composite thin film to determine its definite lattice structure (Fig. 4g). As demonstrated in Figure, NiS₂ and graphene are clearly differentiated from one another, with lattice spacing distances of 0.29 nm and 0.36 nm, respectively, corresponding with NiS₂ and graphene lattice spacing. The chemical compositions of the as developed NiS₂/graphene nanocomposites were also evaluated by EDS analysis (Fig. 4h), which confirmed the existence of C, S, and Ni. Carbon, sulphur, and nickel content (wt%) in NiS₂/graphene are 54.12%, 18.16%, and 27.72%, respectively.

3.4 Surface area analysis

The gas-sensing characteristics of nanostructured materials are inherently connected with the available surface area and porosity. The specific surface area and porosity of NiS₂ and NiS₂/graphene samples were investigated by N₂ adsorption–desorption isotherms. The isotherms of these two samples are shown in Fig. 5a. Both samples display type IV isotherms with small hysteresis loop [32–35]. These results indicate that the pore volumes are supplied by mesopores in these samples, thus, providing efficient channels for mass transport. The presence of mesoporous–structure was apparent and confirmed by Brunauer–Emmett–Teller (BET) data, which showed specific surface areas of 49.7 and 102.8 m²/g for NiS₂

and NiS₂/graphene, respectively. Figure 5b depicts the Barrett–Joyner–Halenda (BJH) results. The NiS₂ and NiS₂/graphene pore pore diameters are 12.89 and 19.12 nm, respectively, confirming the presence of a mesoporous–structure. However, the NiS₂/graphene film exhibiting a high surface area (102.8 m²/g) with porous structure has a large amount of surface active sites for the oxygen adsorption and reaction with detected NO₂ gas molecules. This may enhance the free electron exchange between the surface adsorbed species of the surface and the bulk of the NiS₂ film. Therefore, the sensor having a larger effective surface area can supply a larger amount of surface adsorbed species (O₂[−], O[−] and O₂[−], etc.), resulting in larger changes in the electrical conductivity of the sensor and eventually in obtaining a higher sensitivity.

3.5 XPS analysis

The elemental composition and oxidation states of the NiS₂/graphene hybrid composite were further analyzed by XPS. As shown in Fig. 6a, the full survey scan XPS spectrum confirmed the presence of C, Ni, and S elements in the NiS₂/graphene hybrid composite. In the XPS analysis, binding energy (BE) referencing method is commonly performed with C 1s peak of adventitious carbon (AdC) to determine the chemical-state of specimens. Recent survey on XPS literature shows C 1s peak (E_B^F) position varied over a large range from 284.4 to 285.7 eV reliant on the substrate [36]. The high-magnification C 1s XPS spectrum was divided into two peaks (Fig. 6b) at

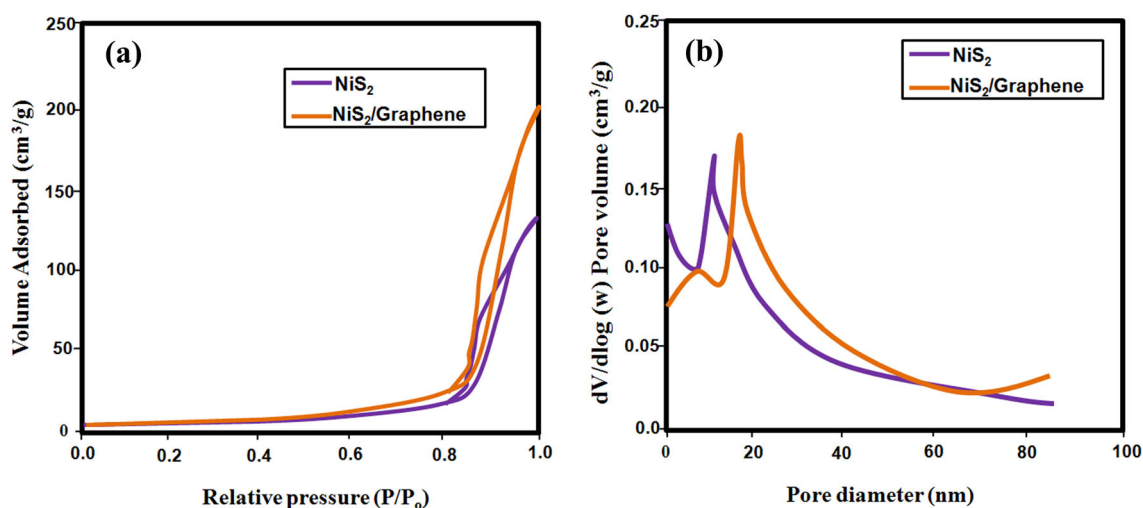


Fig. 5 **a** N₂ adsorption and desorption analysis of graphene, NiS₂, NiS₂/G and **b** corresponding pore size distribution

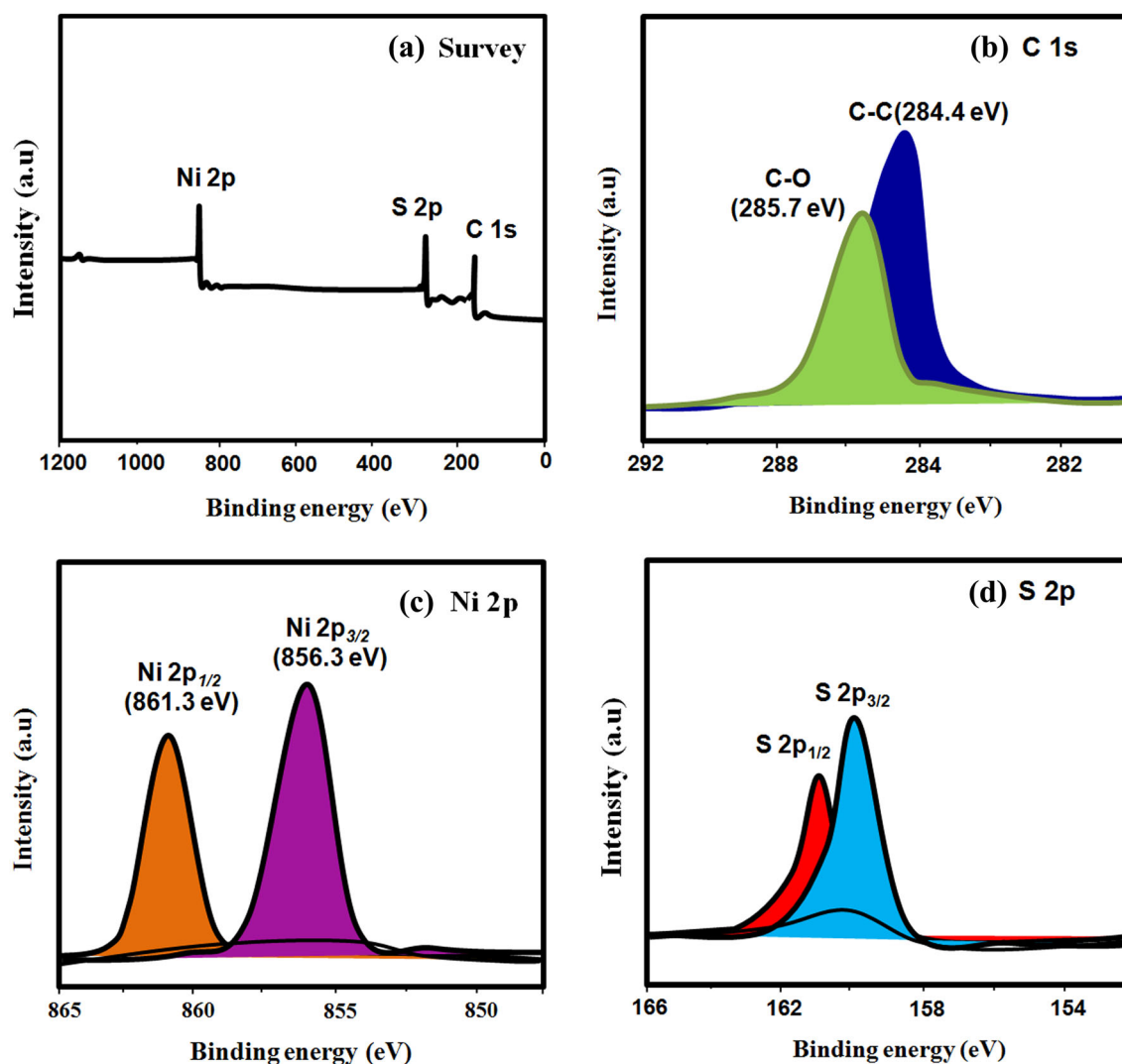


Fig. 6 XPS of NiS₂/graphene **a** survey, **b** C 1s, **c** Ni 2p and **d** S 2p

285.3 eV, which could be assigned to the obvious adventitious carbon [37] and loaded graphitic carbon (C–C bonds) on the sample surface, and at 286.2 eV, which might originate from absorbed gaseous molecules (C–O bonds). The HR XPS peaks of Ni 2p spectrum located at 856.3 (Ni 2p_{3/2}) and 861.6 eV (Ni 2p_{1/2}) correspond to the dominant oxidation state of Ni²⁺ (Fig. 6c). Additionally, S 2p peaks were located at 161.4 and 160.1 eV (Fig. 6d) with a spin–orbit separation of 1.2 eV, corresponding to sulfide in NiS₂ sample [38].

3.6 Gas-sensing test

The prepared sensor films were exposed to air atmosphere in order to find out the resistance

behavior of the thin film sensors. The resistance of the sensor sample was measured as a function of temperature and the temperature is varied from 0 to 400 °C. Figure 7a shows the resistance of the graphene, NiS₂ and NiS₂/graphene composite sensor samples. At RT, the resistance values of graphene, NiS₂, and NiS₂/graphene composite sensors were found to be 34 KΩ, 45 KΩ and 57 KΩ, respectively. At 400 °C, the resistance values of graphene, NiS₂, and NiS₂/graphene composite sensors were found to be 63 KΩ, 84 KΩ and 112 KΩ, respectively. It was clear that the resistance of NiS₂/graphene is higher than pristine graphene and NiS₂, respectively. It can be seen that the resistance values of all the sensor sample drops around at 300 °C. Hence, it was concluded that 300 °C was optimum temperature of the sensor

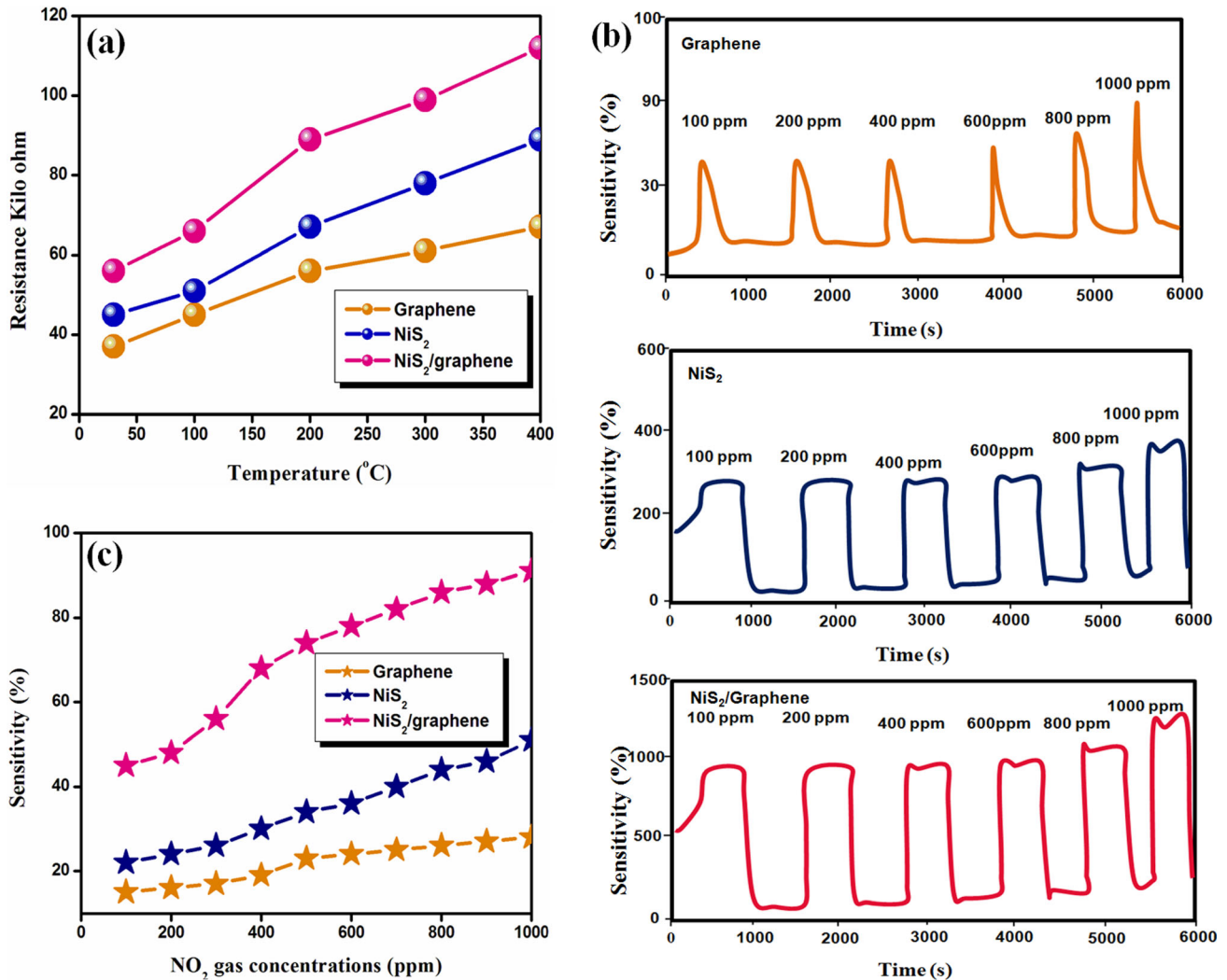


Fig. 7 **a** Resistance variation as a function of temperature, **b** Dynamic response of NO₂ gas and **c** sensitivity plot of all the sensor sample

samples. Therefore, the NO₂ gas-sensing performance of the sensor samples was measured at 300 °C with different concentration. The NO₂ gas concentration was varied from 100 to 1000 ppm, and the dynamic response of the sensor samples were displayed in Fig. 7b. It was clear that sensing response of NiS₂/graphene composite sensor showed superior than compared with graphene and NiS₂. The sensor response is calculated using $S (\%) = \Delta R/R \times 100$, where ΔR is a difference between the gas and air resistance; R is the gas resistance [32]. Figure 7c shows the sensitivity plot of the sensor films. The NiS₂/Graphene sensor had the highest sensitivity (97%) to NO₂ gas at a concentration of 1000 ppm, where as pristine graphene and NiS₂ was found to be 28% and 51%, respectively. The response and recovery time calculated from the dynamic response plot

of Fig. 8a–c indicates a very short response time of 19 s and a recovery time of 37 s for the NiS₂/graphene composite at 1000 ppb concentrations. The response and recovery times for the graphene sensor are 61 s & 48 s and 51 s & 37 s for the NiS₂ sensor. The NO₂ gas sensing parameters of the sensor sample was summarized in Table 1. Surprisingly, the NiS₂/graphene sensor has a faster response time than the other two sensors, but a longer recovery time. The reason for this is the NiS₂/graphene sensor's huge specific surface area and many pores, which are favourable for gas diffusion and monitoring reactions. Due to the presence of water vapour in the exhaust gas, such sensors are typically used in humid conditions. We evaluated the influence of humidity on NO₂ detection with sensors at 300 °C based on our earlier data. The NO₂ gas-sensing parameters of the

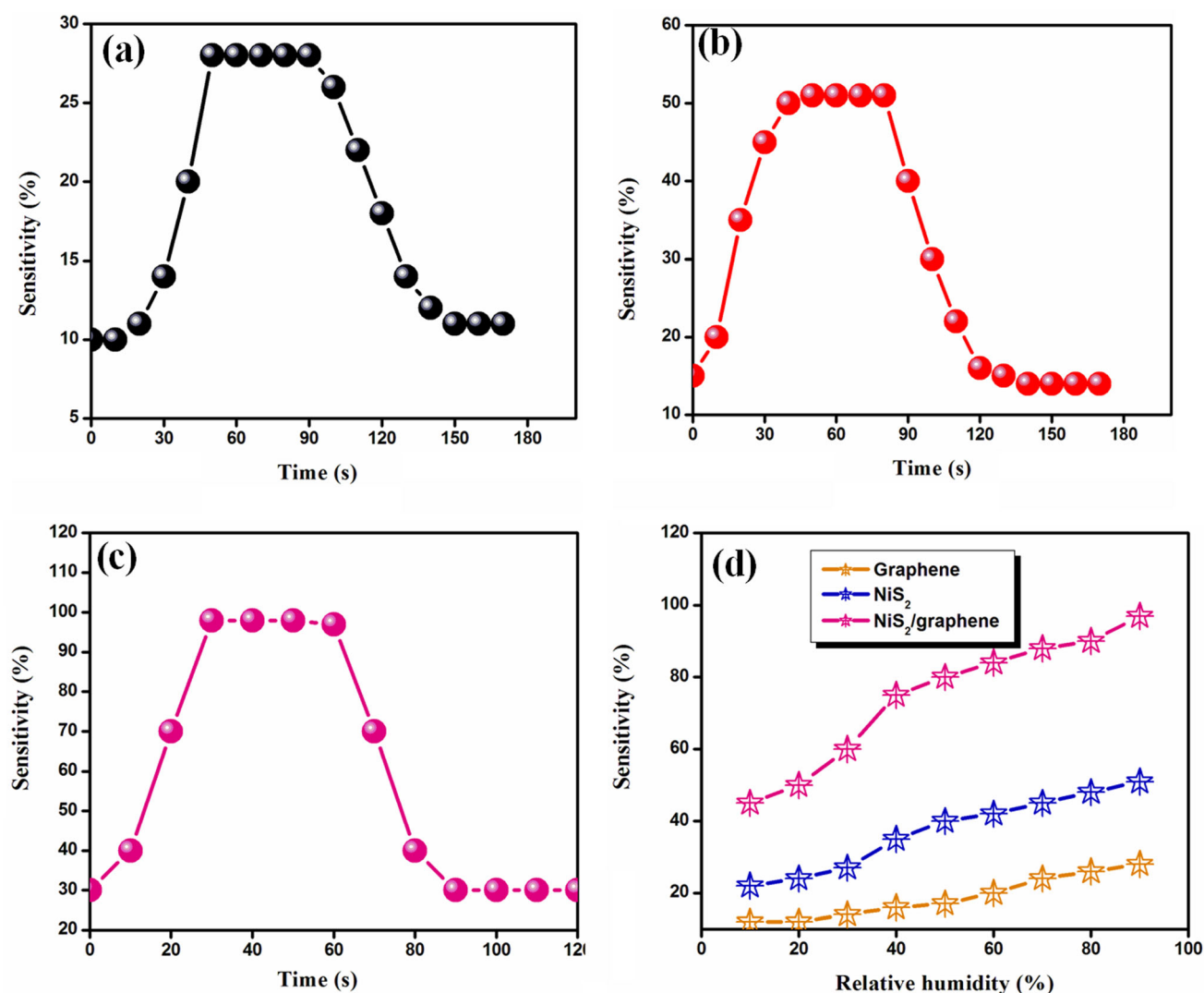


Fig. 8 Response and recovery time of **a** graphene, **b** NiS₂, **c** NiS₂/G, **d** Sensing response as a function of humidity

Table 1 Gas-sensing parameters of the sensor samples

Samples	Sensitivity (%)	Response time (s)	Recovery time (s)
Graphene	28	61	48
NiS ₂	51	51	37
NiS ₂ /graphene	97	34	39

sensors was further evaluated with presence of various humidity levels (0–90%) at 300 °C and the result plot is shown in Fig. 8d. As shown in Fig. 8d, the sensor signal is drop gradually with the increase of humidity level form 10% to 90%. The composite sensor sensing performance was found to be 96, 76, and 70% with the relative humididty level of 30%, 60% and 90%, respectively. Gas sensors must have not only great sensitivity and repeatability, but also strong selectivity to the target gas for practical

applications. As a result, the response of the sensor with graphene, NiS₂, and NiS₂/graphene thin film sensors toward various toxic gases was investigated in order to evaluate its selectivity at the optimum working temperature (300 °C) (e.g., CO₂, H₂, NH₃ and CH₄). The bar diagram (Fig. 9a–c clearly illustrates that all sensors exposed to NO₂ gas have a higher sensing response than other gases. As a result, the sensor has a high selectivity for NO₂ gas as compared to other gases. The long-term stability is

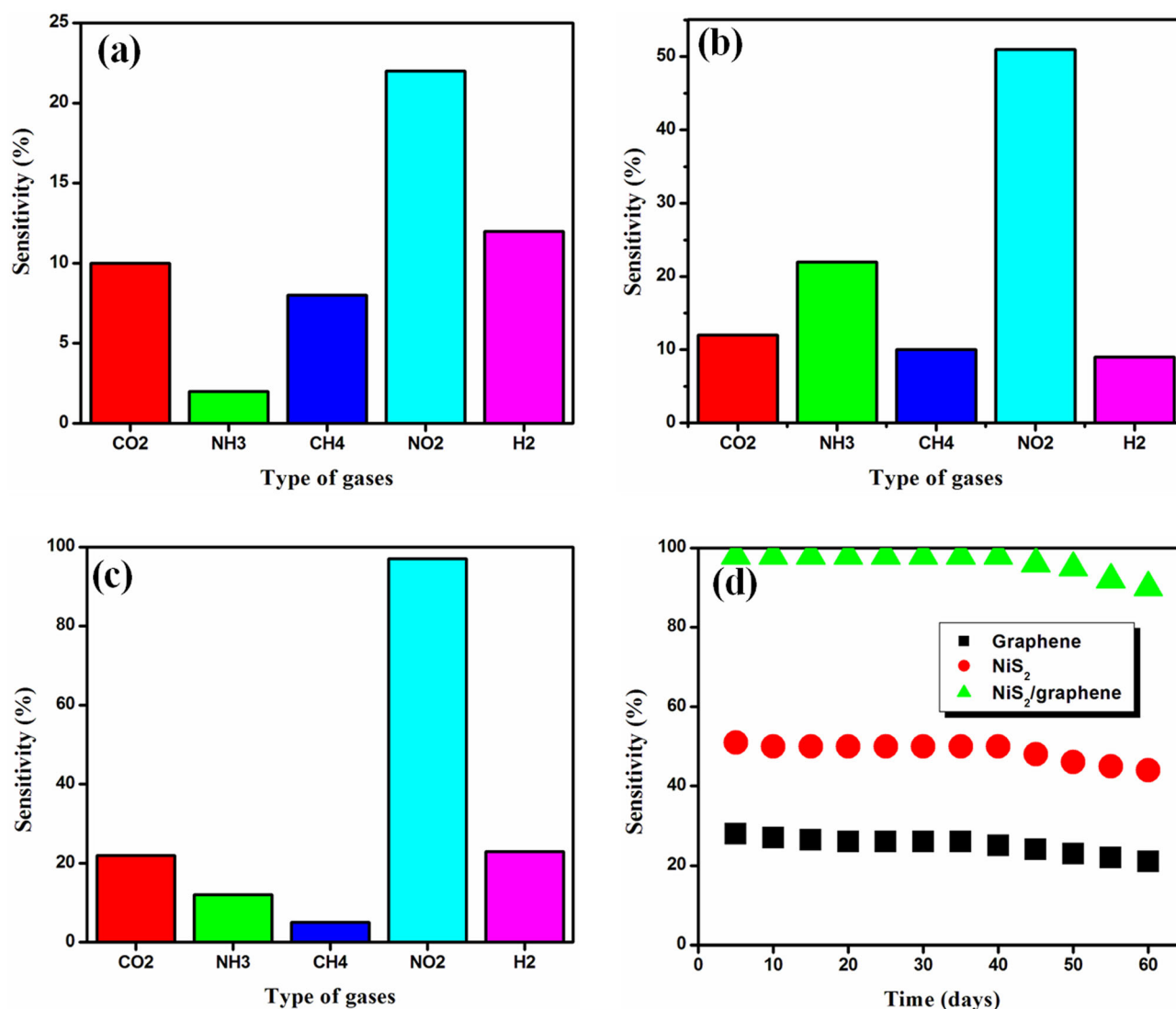


Fig. 9 a Long-term stability; Selectivity response curve of b graphene, c NiS₂, d NiS₂/G

plotted in Fig. 9d. It was clear evident that the NO₂ response was did not change noticeably for the period of 45 days at a testing with 100 ppm level of NO₂ gas. Table 2 compares the NO₂ gas sensing properties of the NO₂ gas sensor suggested in this paper with

those reported elsewhere in the literature [33–35, 39–41]. In order to investigate the effect of graphene incorporation on the photo conducting properties of NiS₂, the current–voltage (I–V) characteristics were recorded. Fig. S5 represents the I–V

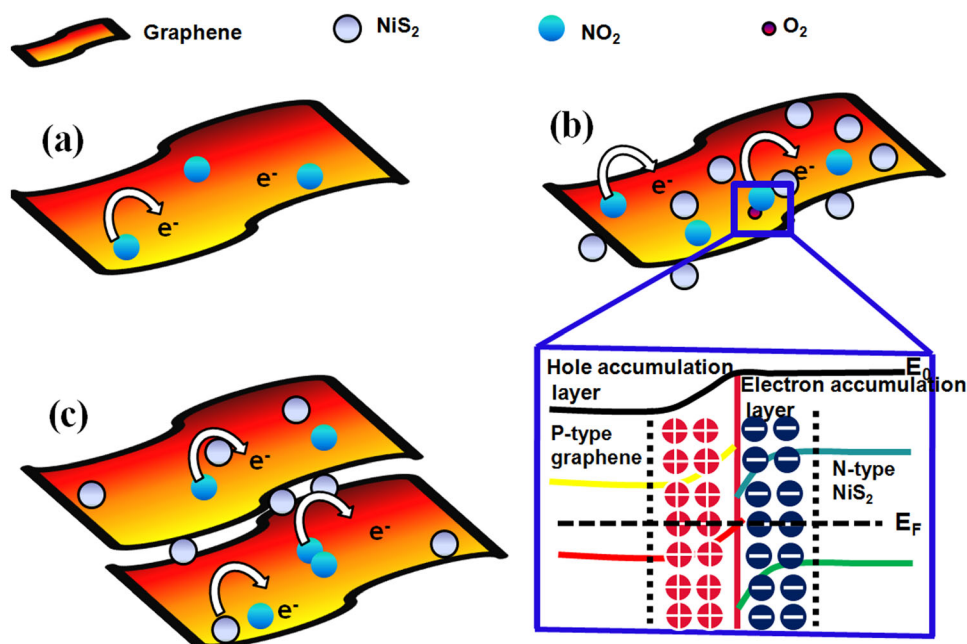
Table 2 Comparison of gas-sensing performances of the NiS₂/graphene composite sensor toward NO₂ with previous works

Sensing materials	Sensor type	NO ₂ (ppm)	Sensitivity	Refs.
MoS ₂	Chemiresistor	100	58	[33]
MoS ₂	Chemiresistor	150	78	[34]
SnO ₂ /graphene	Chemiresistor	200	28	[35]
MoS ₂ /graphene	Chemiresistor	200	31	[39]
SnS ₂	Chemiresistor	200	27	[40]
MoS ₂ /ZnO	Chemiresistor	200	35	[41]
NiS ₂ /graphene	Chemiresistor	100	97	This work

characteristics of pure NiS_2 and NiS_2 /graphene composite films for UV light power density of 750 mW/cm^2 . The linear nature of I–V curve suggests that NiS_2 and NiS_2 /graphene have ohmic contact. Graphene nano-sheets facilitate the carrier transportation in composite films with NiS_2 . With the addition of graphene, the NiS_2 /graphene composite films show enhanced current production under UV irradiation ($\lambda = 374 \text{ nm}$). This can be attributed to the increase in carrier concentration with incorporation of graphene as estimated from optical measurements. In the case of NiS_2 /graphene, the generated charge carriers under illumination travel through the highly conductive graphene layer which is embedded between the NiS_2 particles (morphology as observed in SEM and TEM images). A schematic illustration of sensing mechanism is shown in Fig. 10. For bare graphene layer, as shown in Fig. 10a, the electrons transfer from reducing NO_2 gas molecules to p-type graphene nanosheets and result in a decrease of charge carriers concentration (the resistance increases). After an appropriate amount of graphene nanosheets are deposited on the surface of NiS_2 nanoparticles film, we suggest two kinds of adsorption sites, being related to graphene nanosheets surface and NiS_2 /graphene interfaces, exist in bilayer thin film, in which the latter one might be responsible for the enhancement of sensing properties compared

with pure graphene film. It is noteworthy that although O_2^- could be produced on the surface of NiS_2 nanoparticles even at room temperature (see Fig. 10b), the catalytic oxidation ability of O_2^- is not powerful enough to convert NO_2 as the final product (N_2 and O) when the temperature is lower than 373 K . However, since the work function of p-graphene (4.75 eV) is lower than that of n- NiS_2 (5.20 eV), a considerable amount of local accumulation heterojunctions at interfaces between graphene nanosheets and NiS_2 nanoparticles might be formed at NiS_2 /graphene interfaces, in which more holes and electrons could accumulate in graphene and NiS_2 regions of heterojunction, respectively, as shown in the magnified view of Fig. 10b. In the present case, graphene becomes more p-type than the original state, and thus, the energy barrier between absorbed NO_2 molecules and graphene is further reduced, resulting in the higher response values and shorter response times. The increase of NO_2 sensor response in the presence of humidity can be explained as follows: in the absence of humidity, only adsorbed oxygen occupies all available active sites on the surface of the sensing layer, whereas in the presence of humidity, some active sites will be occupied by water molecules. In other words, in dry condition, more surface adsorbed oxygen implies that more target gas will react with the sensing material, and thus,

Fig. 10 Schematic illustration of NO_2 -sensing mechanism of **a** graphene and **b**, **c** graphene/ NiS_2 film sensor, in which **b** and **c** shows the adsorption sites of graphene/ NiS_2 film with proper and excess rGO amount, respectively, and the magnified view in **(b)** is the formed accumulation heterojunctions at the interface



enhance the sensor response as a result of the reaction between the target gases with the adsorbed oxygen. However, the observed increase of NO₂-selectivity can be ascribed to the achievement of higher affinity between –OH species and NO₂ than other gases. As observed, in the presence of water molecules, NO₂ will be readily adsorbed on the surface than other gases because of the fact that the Van der Waal forces between O–H and NO₂ are stronger than those between O–H and CO. This will lead to the enhancement of NO₂-absorption on the sensing layer than that of other gases resulting in better selectivity toward NO₂.

4 Conclusion

In conclusion, pure NiS₂ and NiS₂/graphene hybrid thin film was successfully deposited by a thermal spray-CVD technique. The sensing properties of the sensor having this NiS₂ and NiS₂/graphene film as sensing material were tested between RT and 400 °C toward various gases (e.g., CO₂, NH₃, CH₄, NO₂ and H₂). The NiS₂ gas sensor responded with a 28% change upon being exposed to 100 ppm of NO₂, while the response of the NiS₂/graphene device reached 97% when exposed to the same NO₂ concentration. The results show that the addition of the NiS₂ nanoparticles to the graphene matrix can improve the sensing performances: firstly, by increasing the sensing response towards NO₂ and secondly by enhancing the selectivity. The introduction of NiS₂ nanoparticles seems mainly affecting the film morphology. NiS₂ nanoparticles prevent graphene sheets from restacking, thus increasing specific surface area. In addition, the preferential placement of the NiS₂ nanoparticles clusters along the flake edges fosters the faster interaction of the NO₂ with the sp² carbon atoms of the graphene sheets. This finally leads to the enhancement of surface properties such as catalytic activity or surface adsorption, essential properties to produce chemical sensors with superior performances. This work demonstrates a promising gas-sensing platform based on NiS₂/graphene heterostructures and could also have implications for broader applications that utilize the unique electronic properties of hybrid 2D graphene/TMDCs heterostructures.

Author contributions

RS, AG, BAA: study conceptualization and writing (original draft) the manuscript. SM, JD: data curation, formal analysis and writing (review & editing), and funding acquisition and project administration.

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Data availability

The data that support the findings of this study are available from the corresponding author, upon reasonable request.

Declarations

Conflict of interest The authors declare they have no conflicts of interest.

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